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(54) **SOLAR CELL AND PREPARATION METHOD THEREFOR**

(57) The present disclosure provides a solar cell and a method for preparing the same. The solar cell includes a semiconductor substrate (100), a first heavily doped layer (111), a front electrode (120), an emitter layer (130), and a back electrode (140). The first heavily doped layer (111) and the front electrode (120) are disposed on the front surface of the semiconductor substrate (100). The first heavily doped layer is disposed between the front electrode (120) and the semiconductor substrate (100). The emitter layer (130) is disposed between the back electrode (140) and the semiconductor substrate (100).

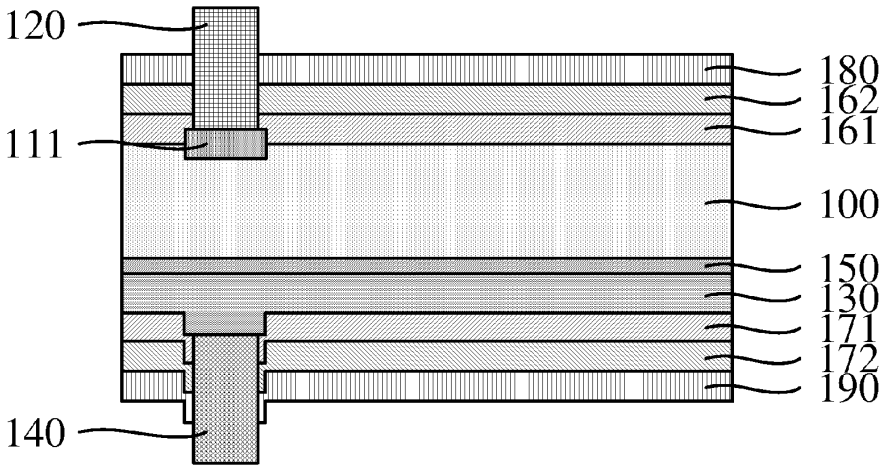

FIG. 1

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